

2N4091, 2N4092, 2N4093

N-Channel Silicon Junction Field-Effect Transistor

- Low $r_{DS(on)}$
- $I_{D(off)} < 100$ pA
- Fast Switching

Absolute maximum ratings at $T_A = 25^\circ\text{C}$

Reverse Gate Source & Gate Drain Voltage	-40V
Continuous Forward Gate Current	10 mA
Continuous Device Power Dissipation	300 mW
Power Derating	1.7 mW/ $^\circ\text{C}$
Storage Temperature Range	-65°C to $+150^\circ\text{C}$

At 25°C free air temperature

		2N4091		2N4092		2N4093		Process NJ132	
Static Electrical Characteristics		Min	Max	Min	Max	Min	Max	Unit	Test Conditions
Gate Source Breakdown Voltage	$V_{(BR)GSS}$	-40		-40		-40		V	$I_G = -1$ uA, $V_{DS} = 0$ V
Gate Reverse Current	I_{GSS}		200		200		200	pA	$V_{GS} = -10$ V, $V_{DS} = 0$ V
Gate Source Cutoff Voltage	$V_{GS(OFF)}$	-5	-10	-2	-7	-1	-5	V	$V_{DS} = 10$ V, $V_{GS} = 0$ V
Drain Saturation Current (pulsed)	I_{DSS}	30		15		5		mA	$V_{DS} = 10$ V, $V_{GS} = 0$ V

Dynamic Electrical Characteristics

Drain -Source On Resistance	$r_{ds(on)}$		30		50		80	Ω	$V_{GS} = 0$ V, $I_D = 0$ V	$f = 1$ kHz
Common-Source Input Capacitance	C_{iss}		16		16		16	pF	$V_{DS} = -10$ V, $V_{GS} = 1$ V	$f = 1$ MHz
Common-Source Reverse Transfer Capacitance	C_{rss}		5		5		5	pF	$V_{DS} = 10$ V, $I_D = 5$ mA	$f = 1$ MHz
Turn-On Delay Time	t_d		15		15		20	nS	$V_{DD} = 10$ V, $V_{GS(on)} = 0$ V	
Rise Time	t_r		10		20		40	nS	$V_{DD} = 10$ V, $V_{GS(on)} = 0$ V	
Turn-Off Time	t_{off}		40		60		80	nS	$V_{DD} = 10$ V, $V_{GS(on)} = 0$ V	

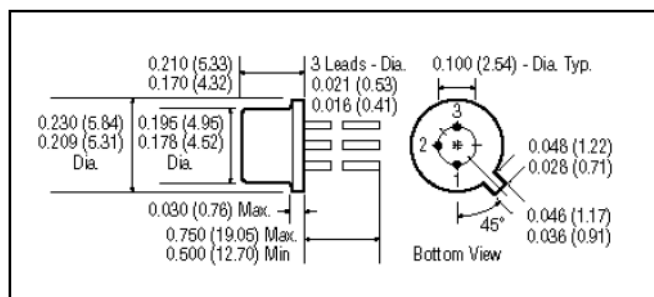
TO-18 Package

Dimensions in Inches (mm)

Pin Configuration

1 Source 1, 2 Gate & Case, 3 Drain

Surface Mount - SMP4091, SMP4092, SMP4093



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